

RQM2201DNS

Silicon N Channel MOS FET Power Switching

REJ03G1492-0200 Rev.2.00 Apr 16, 2007

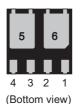
Features

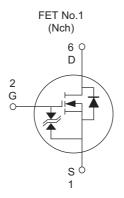
- Small, thin and leadless type package (3×3 mm, t = 0.8 mm max.)
- Two FET chips are mounted in one package
- High density mounting
- High speed switching. (Ciss = 200 pF typ)
- $V_{DSS} \ge 60 \text{ V}$ and capable of 2.5 V gate drive

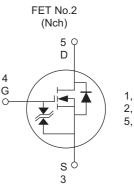
Outline

RENESAS Package code: PWSN0006ZA-A (Package name: WSON0303-6 <HWSON-6>)









1, 3: Source 2, 4: Gate 5, 6: Drain

Notes:

- 1. Marking is "M2201".
- 2. The following maximum ratings and electric characteristics are applied to both FET1 and FET2.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Symbol Ratings	
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±12	V
Drain current	I _D	2	А
Drain peak current	I _{D(pulse)} Note1	8	А
Body - drain diode reverse drain current	I _{DR}	2	А
Channel dissipation	Pch Note2	1	W
Channel dissipation	Pch Note3	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 $\mu s,$ Duty cycle \leq 1%

- 2. 1 Drive operation: When using the glass epoxy board (FR-4 $40 \times 40 \times 1$ mm)
- 3. 2 Drive operation: When using the glass epoxy board (FR-4 $40 \times 40 \times 1$ mm)

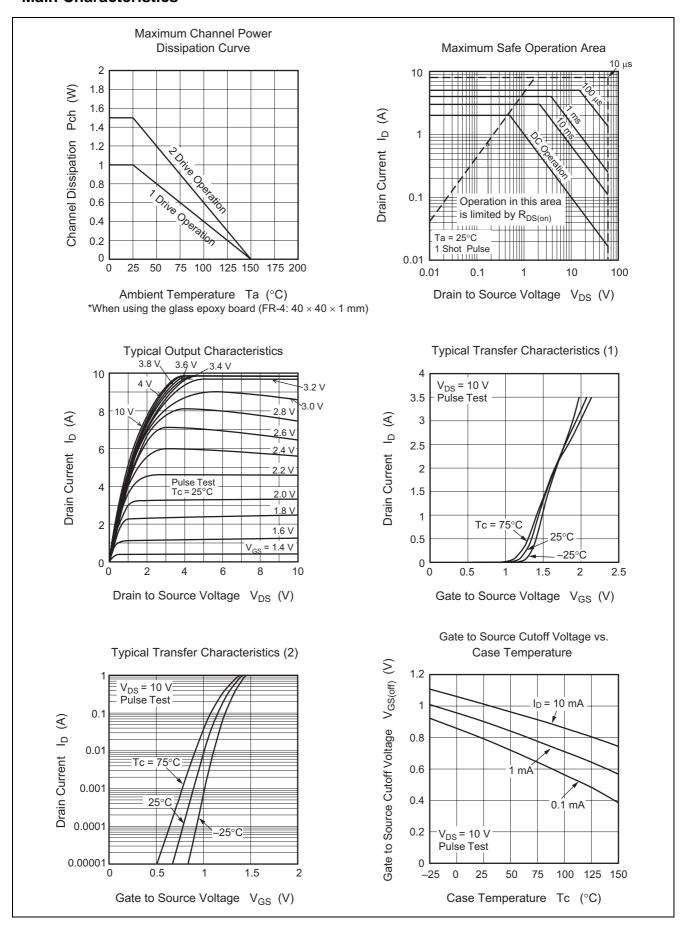
Electrical Characteristics

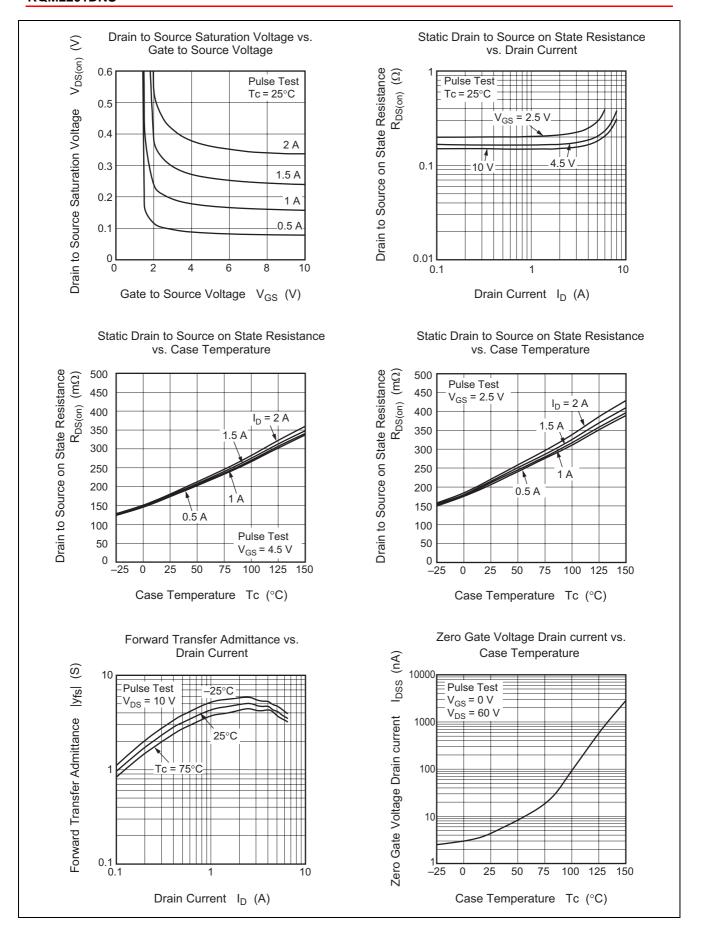
 $(Ta = 25^{\circ}C)$

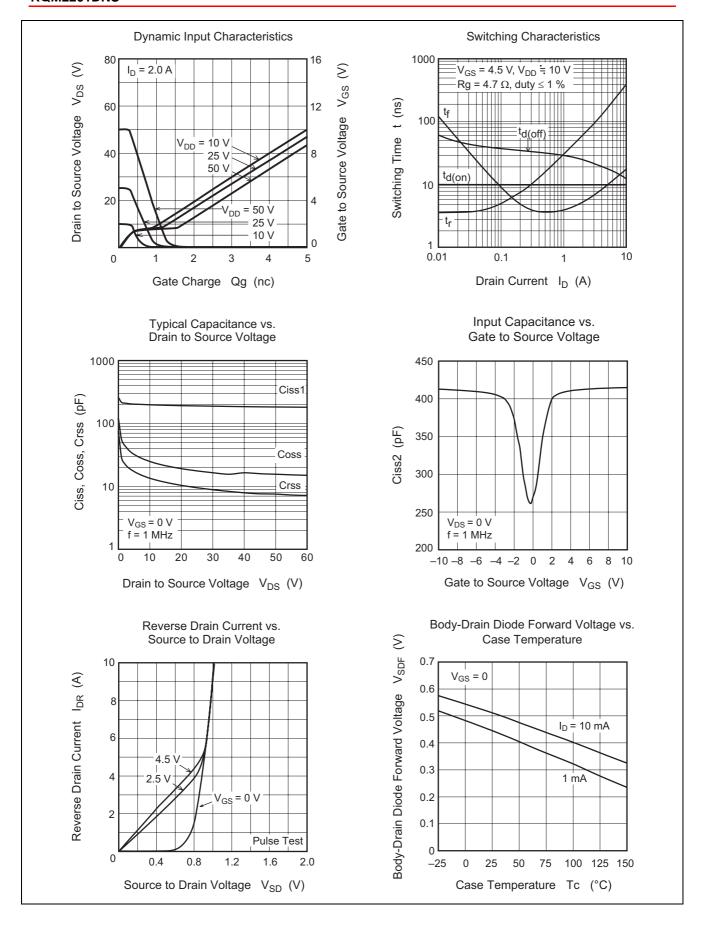
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	$V_{(BR)GSS}$	+12	_	_	V	$I_G = +100 \mu\text{A}, V_{DS} = 0$	
Gate to source breakdown voltage	$V_{(BR)GSS}$	-12	_	_	V	$I_G = -100 \mu\text{A}, V_{DS} = 0$	
Gate to source leak current	I _{GSS}	_	_	+10	μΑ	$V_{GS} = +10 \text{ V}, V_{DS} = 0$	
Gate to source leak current	I _{GSS}	_	_	-10	μΑ	$V_{GS} = -10 \text{ V}, V_{DS} = 0$	
Drain to source leak current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	0.4	_	1.4	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	
Drain to source on state resistance	R _{DS(on)}	_	173	225	mΩ	$I_D = 1 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$	
Drain to source on state resistance	R _{DS(on)}	_	207	290	mΩ	$I_D = 1 \text{ A}, V_{GS} = 2.5 \text{ V}^{\text{Note4}}$	
Forward transfer admittance	y _{fs}	2.3	3.5	_	S	$I_D = 1 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$	
Input capacitance	Ciss	_	200	_	pF	V _{DS} = 10 V	
Output capacitance	Coss	_	25	_	pF	$V_{GS} = 0$	
Reverse transfer capacitance	Crss	_	13	_	pF	f = 1 MHz	
Turn - on delay time	t _{d(on)}	_	7	_	ns	I _D = 1 A	
Rise time	t _r	_	28	_	ns	V _{GS} = 10 V	
Turn - off delay time	t _{d(off)}	_	30	_	ns	$R_L = 10 \Omega$	
Fall time	t _f	_	4	_	ns	$Rg = 4.7 \Omega$	
Total gate charge	Qg		2.4	_	nC	V _{DD} = 10 V	
Gate to Source charge	Qgs	_	0.4	_	nC	$V_{GS} = 4.5 \text{ V}$	
Gate to drain charge	Qgd	_	0.4	_	nC	$I_D = 2 A$	
Body - drain diode forward voltage	V_{DF}	_	0.8	_	V	$I_F = 2 A$, $V_{GS} = 0$ Note4	

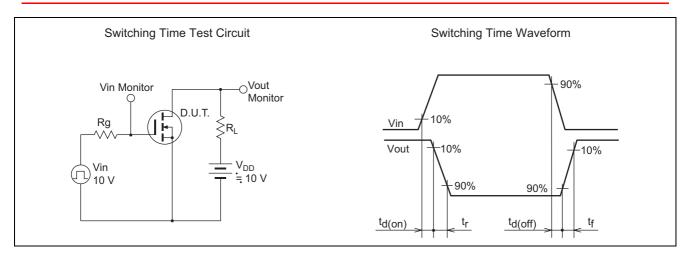
Notes: 4. Pulse test

Main Characteristics

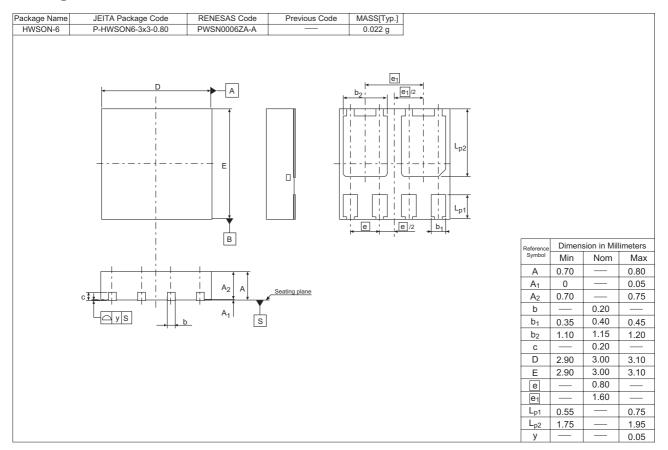








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RQM2201DNSTL-E	2000 pcs.	φ178 mm reel, 8 mm Emboss taping
RQM2201DNSTR-E	2000 pcs.	φ178 mm reel, 8 mm Emboss taping

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510